

## N-Channel Power MOSFET

30V, 78A, 3.8mΩ

### FEATURES

- Low  $R_{DS(on)}$  to minimize conductive losses
- Low gate charge for fast power switching
- 100% UIS and  $R_g$  tested
- Compliant to RoHS directive 2011/65/EU and in accordance to WEEE 2002/96/EC
- Halogen-free according to IEC 61249-2-21

### KEY PERFORMANCE PARAMETERS

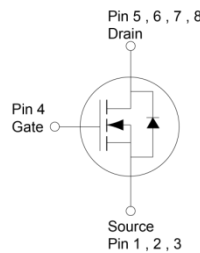
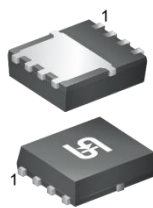
PARAMETER	VALUE	UNIT
$V_{DS}$	30	V
$R_{DS(on)}$ (max)	$V_{GS} = 10V$	3.8
	$V_{GS} = 4.5V$	5.5
$Q_g$	24	nC

### APPLICATIONS

- DC-DC Converters
- Battery Power Management
- ORing FET/Load Switching



PDFN33



Note: MSL 1 (Moisture Sensitivity Level) per J-STD-020

### ABSOLUTE MAXIMUM RATINGS ( $T_A = 25^\circ\text{C}$ unless otherwise noted)

PARAMETER	SYMBOL	LIMIT	UNIT
Drain-Source Voltage	$V_{DS}$	30	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$	V
Continuous Drain Current (Note 1)	$I_D$	$T_C = 25^\circ\text{C}$	78
		$T_A = 25^\circ\text{C}$	19
Pulsed Drain Current	$I_{DM}$	312	A
Single Pulse Avalanche Current (Note 2)	$I_{AS}$	26	A
Single Pulse Avalanche Energy (Note 2)	$E_{AS}$	101	mJ
Total Power Dissipation	$P_D$	$T_C = 25^\circ\text{C}$	39
		$T_C = 125^\circ\text{C}$	7.8
Total Power Dissipation	$P_D$	$T_A = 25^\circ\text{C}$	2.4
		$T_A = 125^\circ\text{C}$	0.5
Operating Junction and Storage Temperature Range	$T_J, T_{STG}$	- 55 to +150	$^\circ\text{C}$

### THERMAL PERFORMANCE

PARAMETER	SYMBOL	LIMIT	UNIT
Junction to Case Thermal Resistance	$R_{\theta JC}$	3.2	$^\circ\text{C/W}$
Junction to Ambient Thermal Resistance	$R_{\theta JA}$	53	$^\circ\text{C/W}$

**Thermal Performance Note:**  $R_{\theta JA}$  is the sum of the junction-to-case and case-to-ambient thermal resistances. The case-thermal reference is defined at the solder mounting surface of the drain pins.  $R_{\theta JA}$  is guaranteed by design while  $R_{\theta CA}$  is determined by the user's board design.

**ELECTRICAL SPECIFICATIONS** ( $T_A = 25^\circ\text{C}$  unless otherwise noted)

PARAMETER	CONDITIONS	SYMBOL	MIN	TYP	MAX	UNIT
<b>Static</b>						
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = 250\mu A$	$BV_{DSS}$	30	--	--	V
Gate Threshold Voltage	$V_{GS} = V_{DS}, I_D = 250\mu A$	$V_{GS(TH)}$	1.2	1.6	2.5	V
Gate-Source Leakage Current	$V_{GS} = \pm 20V, V_{DS} = 0V$	$I_{GSS}$	--	--	$\pm 100$	nA
Drain-Source Leakage Current	$V_{GS} = 0V, V_{DS} = 30V$	$I_{DSS}$	--	--	1	$\mu A$
	$V_{GS} = 0V, V_{DS} = 30V$ $T_J = 125^\circ\text{C}$		--	--	100	
Drain-Source On-State Resistance (Note 3)	$V_{GS} = 10V, I_D = 19A$	$R_{DS(on)}$	--	3	3.8	m $\Omega$
	$V_{GS} = 4.5V, I_D = 16A$		--	4	5.5	
Forward Transconductance (Note 3)	$V_{DS} = 5V, I_D = 19A$	$g_{fs}$	--	48	--	S
<b>Dynamic</b> (Note 4)						
Total Gate Charge	$V_{GS} = 10V, V_{DS} = 15V,$ $I_D = 19A$	$Q_g$	--	48	--	nC
Total Gate Charge	$V_{GS} = 4.5V, V_{DS} = 15V,$ $I_D = 16A$	$Q_g$	--	24	--	
Gate-Source Charge		$Q_{gs}$	--	6.9	--	
Gate-Drain Charge		$Q_{gd}$	--	11	--	
Input Capacitance	$V_{GS} = 0V, V_{DS} = 15V$ $f = 1.0\text{MHz}$	$C_{iss}$	--	2557	--	pF
Output Capacitance		$C_{oss}$	--	380	--	
Reverse Transfer Capacitance		$C_{rss}$	--	276	--	
Gate Resistance	$f = 1.0\text{MHz}$	$R_g$	0.5	1.5	3	$\Omega$
<b>Switching</b> (Note 4)						
Turn-On Delay Time	$V_{GS} = 10V, V_{DS} = 15V,$ $I_D = 19A, R_G = 2\Omega,$	$t_{d(on)}$	--	11	--	ns
Turn-On Rise Time		$t_r$	--	80	--	
Turn-Off Delay Time		$t_{d(off)}$	--	33	--	
Turn-Off Fall Time		$t_f$	--	65	--	
<b>Source-Drain Diode</b>						
Forward Voltage (Note 3)	$V_{GS} = 0V, I_S = 19A$	$V_{SD}$	--	--	1	V
Reverse Recovery Time	$I_S = 19A,$ $di/dt = 100A/\mu s$	$t_{rr}$	--	33	--	ns
Reverse Recovery Charge		$Q_{rr}$	--	19	--	nC

**Notes:**

- Silicon limited current only.
- $L = 0.3\text{mH}, V_{GS} = 10V, V_{DD} = 25V, R_G = 25\Omega, I_{AS} = 26A,$  Starting  $T_J = 25^\circ\text{C}$
- Pulse test: Pulse Width  $\leq 300\mu s,$  duty cycle  $\leq 2\%$ .
- Switching time is essentially independent of operating temperature.

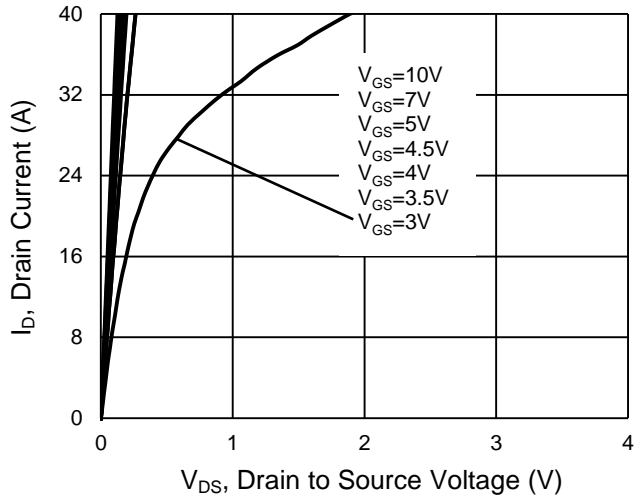
**ORDERING INFORMATION**

PART NO.	PACKAGE	PACKING
TSM038N03PQ33 RGG	PDFN33	5,000pcs / 13" Reel

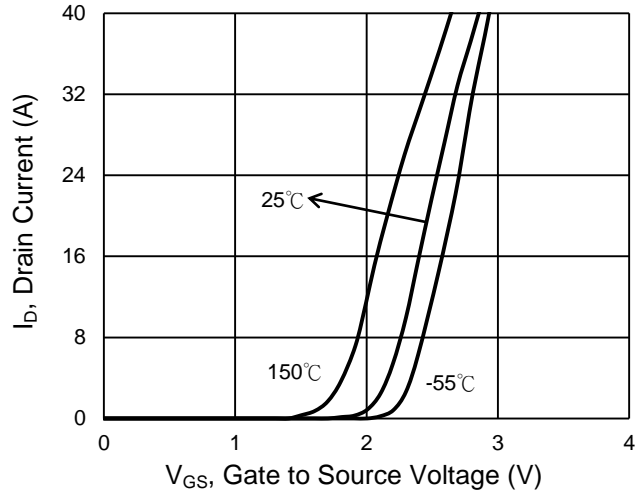
**CHARACTERISTICS CURVES**

( $T_A = 25^\circ\text{C}$  unless otherwise noted)

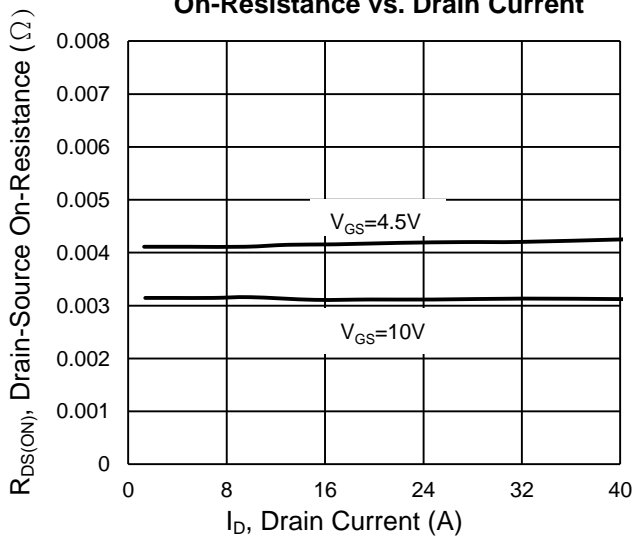
**Output Characteristics**



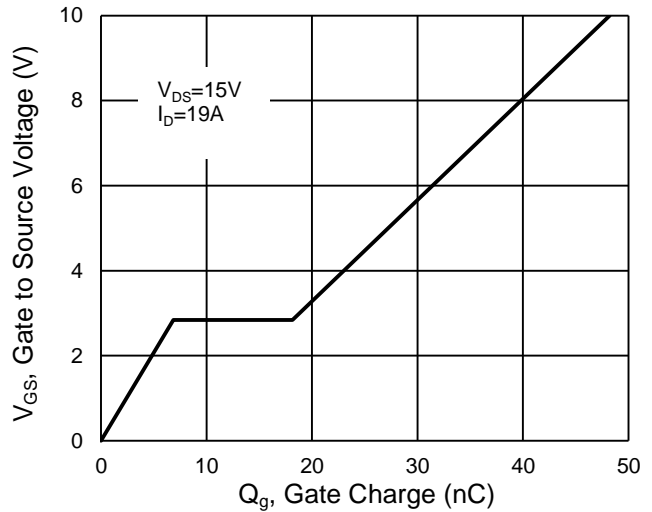
**Transfer Characteristics**



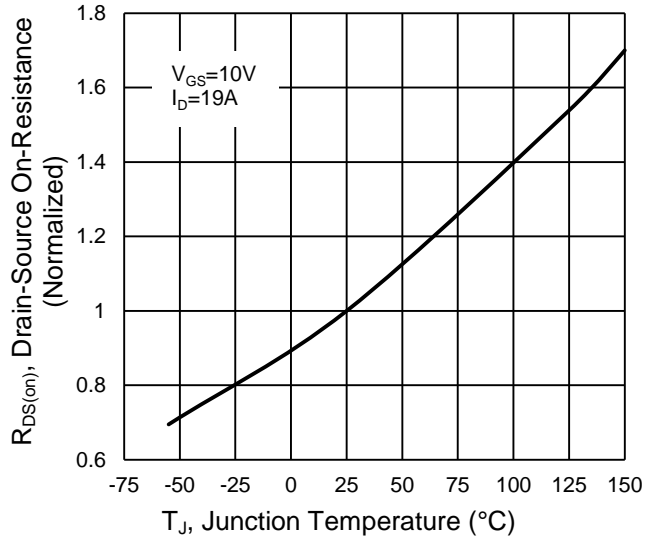
**On-Resistance vs. Drain Current**



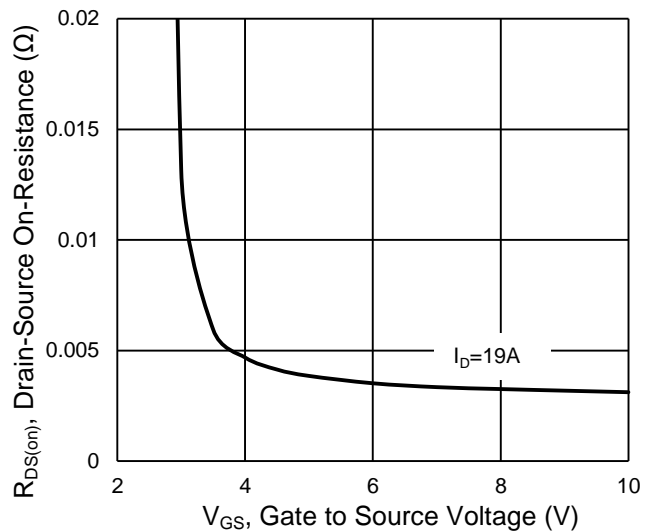
**Gate-Source Voltage vs. Gate Charge**



**On-Resistance vs. Junction Temperature**



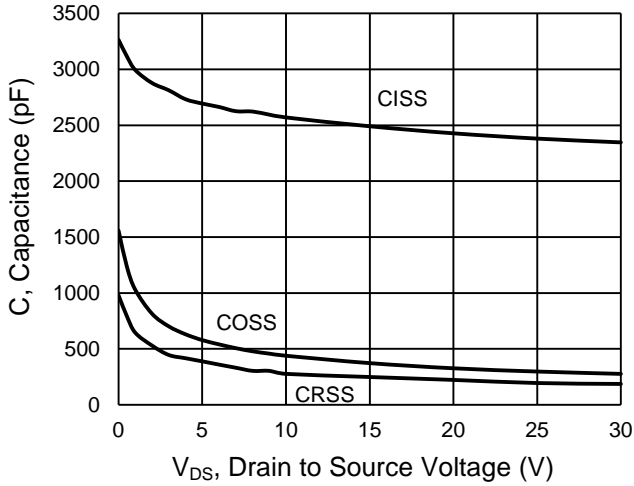
**On-Resistance vs. Gate-Source Voltage**



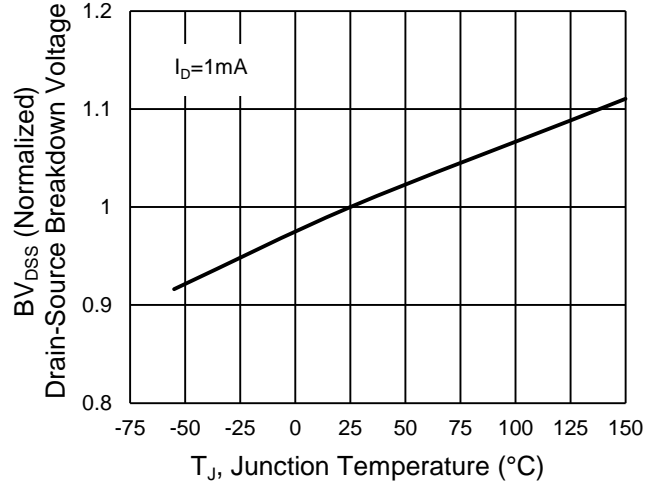
**CHARACTERISTICS CURVES**

( $T_A = 25^\circ\text{C}$  unless otherwise noted)

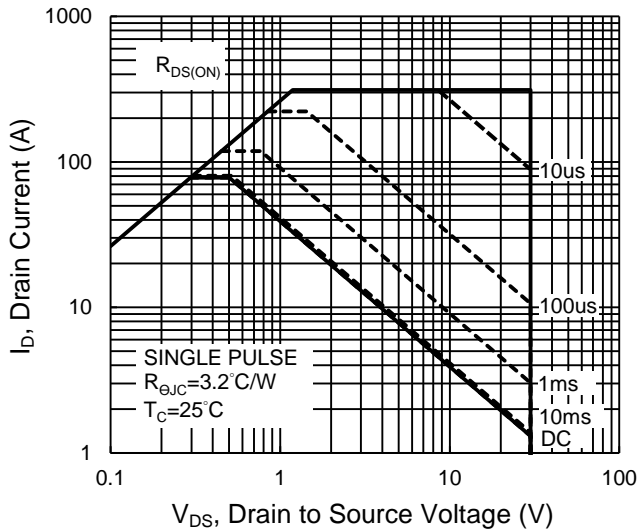
**Capacitance vs. Drain-Source Voltage**



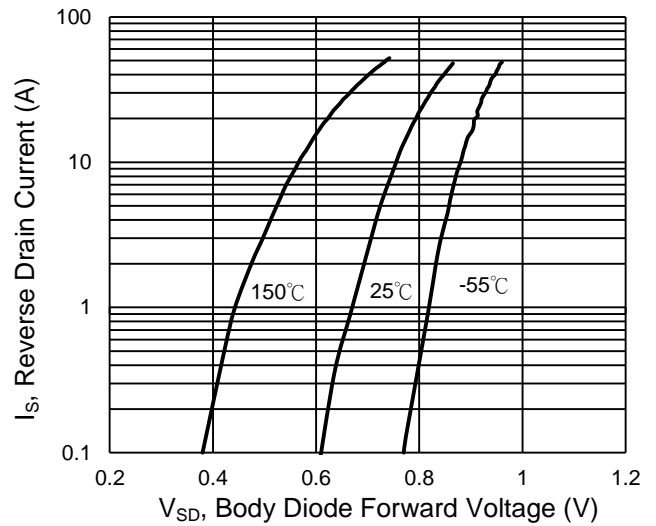
**$BV_{DSS}$  vs. Junction Temperature**



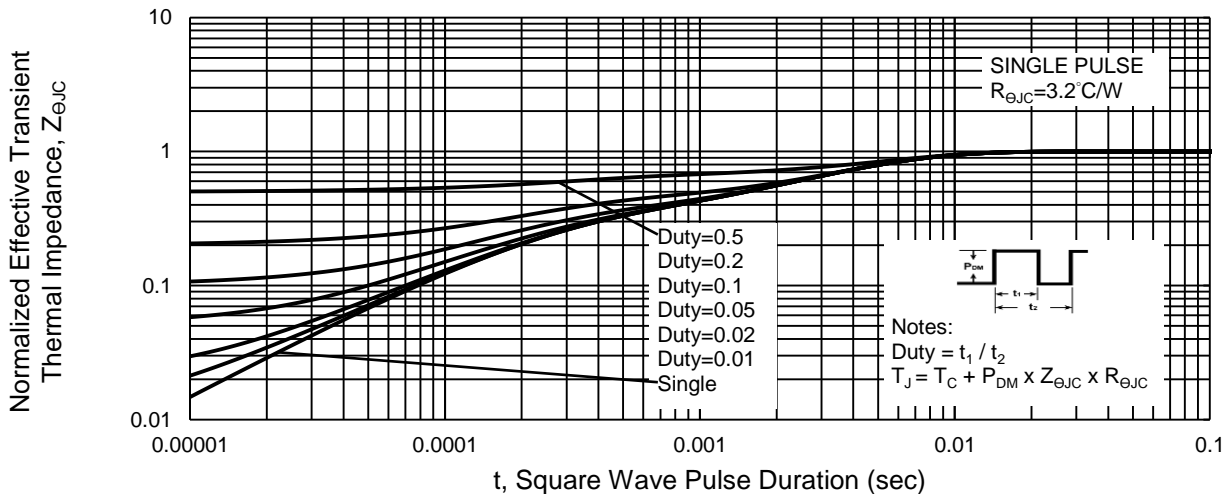
**Maximum Safe Operating Area, Junction-to-Case**



**Source-Drain Diode Forward Current vs. Voltage**

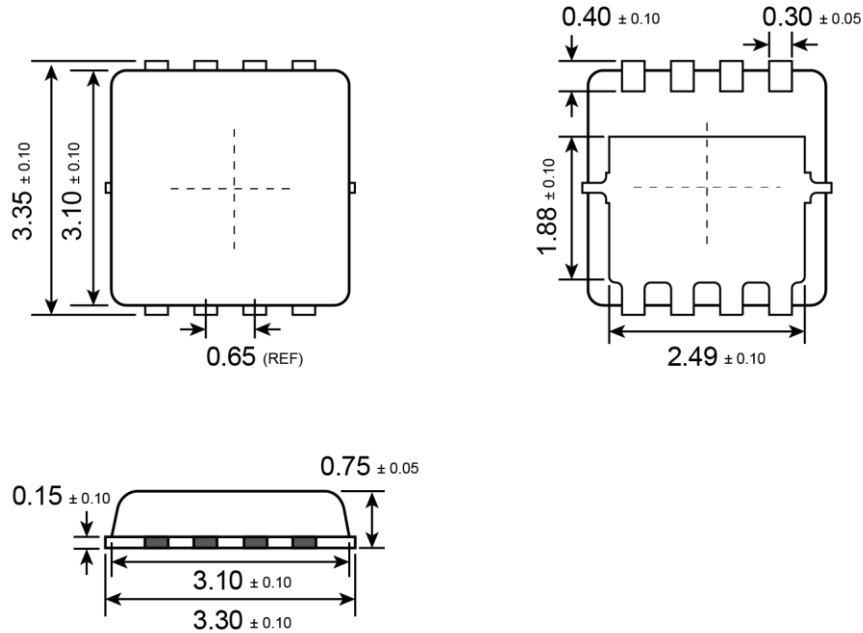


**Normalized Thermal Transient Impedance, Junction-to-Case**

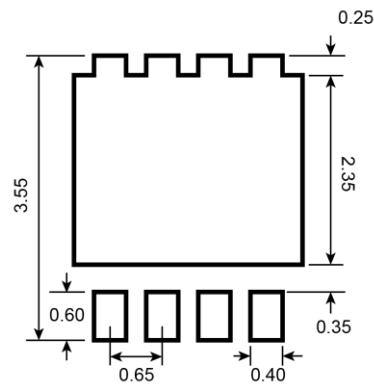


**PACKAGE OUTLINE DIMENSIONS** (Unit: Millimeters)

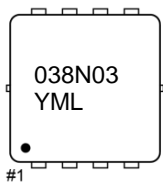
**PDFN33**



**SUGGESTED PAD LAYOUT** (Unit: Millimeters)



**MARKING DIAGRAM**



- Y** = Year Code
- M** = Month Code
- O** =Jan    **P** =Feb    **Q** =Mar    **R** =Apr
- S** =May    **T** =Jun    **U** =Jul    **V** =Aug
- W** =Sep    **X** =Oct    **Y** =Nov    **Z** =Dec
- L** = Lot Code (1~9, A~Z)

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